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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

AMENDMENT "D" ACCOMPANYING RCE

APPLICANTS: Fumihiko Nakamura et al. ATTY DOCKET NO: 09792909-5122  
SERIAL NO.: 09/925,153 GROUP ART UNIT: 2813  
DATE FILED: August 8, 2001 EXAMINER: David Blum  
INVENTION: "INSULATING NITRIDE LAYER AND PROCESS FOR ITS  
FORMING, AND SEMICONDUCTOR DEVICE AND PROCESS  
FOR ITS PRODUCTION"

Commissioner for Patents  
Washington, DC 20231

S I R:

This Amendment "D" accompanies an RCE and is filed in response to the Final Office Action of November 5, 2002. Please reconsider the application in view of the amendment and remarks presented below.

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IN THE DRAWINGS

Corrected drawing Figures 12, 13, and 14 are submitted with the Submission of Corrected Drawings submitted herewith.

IN THE CLAIMS

Please amend claims 1, 2, 4, 13, 16, and 18 as follows:

B<sup>1</sup> 1. (Twice Amended) An insulating nitride layer formed as a buffer layer from a group III-V nitride compound semiconductor heavily doped mostly with cadmium.

B<sup>2</sup> 2. (Amended) An insulating nitride layer as defined in Claim 1, which is heavily doped substantially with said cadmium as an impurity.

B<sup>3</sup> 4. (Amended) An insulating nitride layer as defined in Claim 1, which is doped with said cadmium in an amount not less than  $1 \times 10^{17}/\text{cm}^3$ .